

IN THE CLAIMS:

Please amend Claims 1, 5, 13, 14, 19, and 22 as follows.

1. (Twice Amended / Presently Amended) A method of pattern etching a noble metal layer ~~disposed on a substrate~~ to form an electrode in a RAM capacitor, comprising the steps of:

a) providing a substrate supporting a barrier layer, a noble metal layer on said barrier layer, a protective layer on said noble metal layer, a mask layer on said protective layer, and a patterned resist layer on said mask layer, wherein said protective layer and said mask layer comprise inorganic materials;

b) pattern etching said mask layer using a plasma generated from an etchant gas to expose a portion of said protective layer;

c) removing said patterned resist layer from said mask layer;

d) pattern etching said protective layer to expose a portion of said noble metal layer;

e) heating said noble metal layer to a temperature ranging from about 150°C to about 500°C;

f) pattern etching said noble metal layer using a plasma generated from an etchant gas selected from the group consisting of a halogen containing gas, a noble gas, nitrogen, oxygen, and mixtures thereof;

g) removing said mask layer from said protective layer; and

h) pattern etching said barrier layer using a plasma generated from an etchant gas, to expose a portion of said substrate.

2. (Once Amended / Previously Amended) The method of Claim 1 wherein, after completion of step g), there is residual noble metal on a surface of said barrier layer, and wherein said method comprises an additional step g-2) after step g), in which said residual noble metal is removed from said barrier layer prior to said step (h) pattern etching of said barrier layer.

3. (Once Amended / Previously Amended) The method of Claim 1 wherein said method comprises an additional step g-2) after step g), in which residual protective layer material is removed from said noble metal layer.

4. (Once Amended / Previously Amended) The method of Claim 1 wherein, after completion of step g), there is residual noble metal on a surface of said barrier layer, and wherein said method comprises an additional step g-2) after step g), in which said residual noble metal and any remaining protective layer material are removed prior to said step (h) pattern etching of said barrier layer.

5. (Twice Amended / Presently Amended) The method of Claim 3 1 wherein said ~~removing of said~~ protective layer is removed from said noble metal layer ~~is simultaneous with~~ during pattern etching of said ~~noble metal~~ barrier layer.

6. (Original) The method of Claim 1 wherein said mask layer comprises CVD SiO₂.

7. (Once Amended / Previously Amended) The method of Claim 2 wherein said mask layer and said substrate each comprises CVD SiO₂.

8. (Original) The method of Claim 4 wherein said mask layer comprises CVD SiO₂.

9. (Once Amended / Previously Amended) The method of Claim 1 wherein said mask layer comprises a compound selected from the group consisting of TEOS, CVD SiO₂, Si₃N₄, BSG, PSG, BPSG, and mixtures thereof.

10. (Original) The method of Claim 1 wherein said barrier layer comprises a compound selected from the group consisting of TiN, TiSiN, Ti, WN, TaN, TaSiN, Ta, and mixtures thereof.

B,
Cont.

11. (Original) The method of Claim 1 wherein said protective layer comprises a compound selected from the group consisting of TiN, TiSiN, Ti, WN, TaN, TaSiN, Ta, and mixtures thereof.

12. (Original) The method of Claim 1 wherein said mask layer has a thickness ranging from about 6000Å to about 9,000Å.

13. (Twice Amended / Presently Amended) A method of pattern etching a noble metal layer ~~disposed on a substrate to form an electrode in a RAM capacitor~~, comprising the steps of:

a) providing a substrate supporting a barrier layer, a noble metal layer on said barrier layer, an inorganic mask layer on said noble metal layer, and a patterned resist layer on said mask layer;

b) pattern etching said mask layer using a plasma generated from an etchant gas to expose a portion of said noble metal layer;

c) removing said patterned resist layer from said mask layer;

d) heating said noble metal layer to a temperature ranging from about 150°C to about 500°C;

e) pattern etching said noble metal layer using a plasma generated from an etchant gas selected from the group consisting of a halogen containing gas, a noble gas, nitrogen, oxygen, and mixtures thereof;

f) removing said mask layer from said etched noble metal layer; and

g) pattern etching said barrier layer using a plasma generated from an etchant gas to expose a portion of said substrate.

14. (Twice Amended / Presently Amended) A method of pattern etching a noble metal layer ~~disposed on a substrate to form an electrode in a RAM capacitor~~, comprising the steps of:

B,
Cont.



a) providing a substrate supporting a barrier layer, a noble metal layer on said barrier layer, a protective layer on said noble metal layer, a mask layer on said protective layer, and a patterned resist layer on said mask layer, wherein said protective layer and said mask layer comprise inorganic materials;

b) pattern etching said mask layer using a plasma generated from an etchant gas to expose a portion of said protective layer;

c) removing said patterned resist layer from said mask layer;

d) pattern etching said protective layer to expose a portion of said noble metal layer ;

e) pattern etching said noble metal layer using a plasma generated from an etchant gas selected from the group consisting of a halogen containing gas, a noble gas, nitrogen, oxygen, and mixtures thereof, at a substrate temperature between about 150°C and about 500°C;

f) pattern etching said barrier layer using a plasma generated from an etchant gas to expose a portion of said substrate; and

g) removing said mask layer from said protective layer.

15. (Original) The method of Claim 14 wherein said barrier layer comprises a compound selected from the group consisting of TiN, TiSiN, Ti, WN, TaN, TaSiN, Ta, and mixtures thereof.

16. (Original) The method of Claim 14 wherein said protective layer comprises a compound selected from the group consisting of TiN, TiSiN, Ti, WN, TaN, TaSiN, Ta, and mixtures thereof.

17. (Original) The method of Claim 14 wherein said mask layer has a thickness ranging from about 6000Å to about 9,000Å.

18. (Once Amended / Previously Amended) The method of Claim 14 wherein said mask layer comprises a compound selected from the group consisting of TEOS, CVD SiO₂, Si₃N₄, BSG, PSG, BPSG, and mixtures thereof.

19. (Twice Amended / Presently Amended) A method of pattern etching a noble metal layer ~~disposed on a substrate to form an electrode in a RAM capacitor~~, comprising the steps of:

a) providing a substrate supporting an etch-stop layer, a barrier layer on said etch-stop layer, a noble metal layer on said barrier layer, an inorganic mask layer on said noble metal layer, and a patterned resist layer on said mask layer;

b) pattern etching said mask layer using a plasma generated from an etchant gas to expose a portion of said noble metal layer;

c) removing said patterned resist layer from said mask layer;

B.
cont.
d) pattern etching said noble metal layer using a plasma generated from an etchant gas consisting essentially of a halogen containing gas, a noble gas, and an additive selected from the group consisting of HBr, BCl₃, and mixtures thereof, at a substrate temperature between about 150°C and about 500°C;

e) pattern etching said barrier layer to expose a portion of said etch-stop layer; and

f) removing said mask layer from said etched noble metal layer.

20. (Once Amended / Previously Amended) The method of Claim 19 wherein said method additionally comprises the step of etching said etch-stop layer.

21. (Once Amended / Previously Amended) The method of Claim 19 wherein said mask layer comprises a compound selected from the group consisting of TEOS, CVD SiO₂, Si₃N₄, BSG, PSG, BPSG, and mixtures thereof.

22. (Twice Amended / Presently Amended) A method of pattern etching a noble metal layer ~~disposed on a substrate~~ to form an electrode in a RAM capacitor, comprising the steps of:

a) providing a substrate supporting a barrier layer, a noble metal layer on said barrier layer, a first mask layer on said noble metal layer, a second mask layer ~~on~~ directly overlying said first mask layer, and a patterned resist layer on said second mask layer, wherein said first mask layer and said second mask layer comprise inorganic materials;

b) pattern etching said second mask layer using a plasma generated from an etchant gas to expose a portion of said first mask layer;

c) pattern etching said first mask layer to expose a portion of said noble metal layer;

d) removing said patterned resist layer from said second mask layer;

e) pattern etching said noble metal layer and said second mask layer using a plasma generated from an etchant gas selected from the group consisting of a halogen containing gas, a noble gas, nitrogen, oxygen, and mixtures thereof, at a substrate temperature between about 150°C and about 500°C;

f) pattern etching said barrier layer; and

g) removing said first mask layer from said etched noble metal layer.

23. (Once Amended / Previously Amended) The method of Claim 22 wherein said patterned resist layer is removed from said second mask layer during etching of said first mask layer.

24. (Once Amended / Previously Amended) The method of Claim 22 wherein said first mask layer comprises a compound selected from the group consisting of Si_3N_4 , BSG, PSG, BPSG, and mixtures thereof.

B₁
Cont.

25. (Original) The method of Claim 22 wherein said second mask layer comprises a compound selected from the group consisting of CVD SiO₂, TEOS, Si₃N₄, BSG, PSG, BPSG, SiC, and mixtures thereof.

26. (Original) The method of Claim 22 wherein said first mask layer has a thickness ranging from about 3000Å to about 8000Å.

B₁
cont. 27. (Original) The method of Claim 22 wherein said second mask layer has a thickness ranging from about 500Å to about 4000Å.

28. (Once Amended / Previously Amended) The method of Claim 22 wherein said substrate is etched during etching of said barrier layer.
